

Diodes

# Schottky barrier diode

## RB411VA-50

●Applications

General rectification

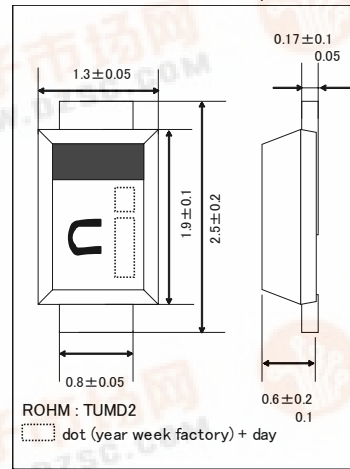
●Features

- 1) Small mold type. (TUMD2)
- 2) High reliability.

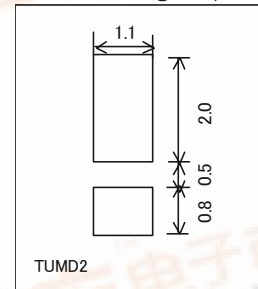
●Construction

Silicon epitaxial planar

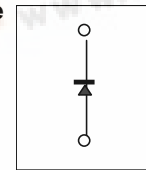
● External dimensions (Unit : mm)



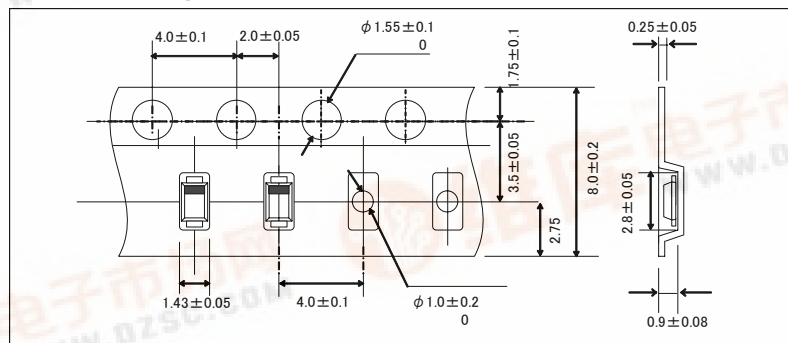
● Land size figure (Unit : mm)



●Structure



● Taping specifications (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

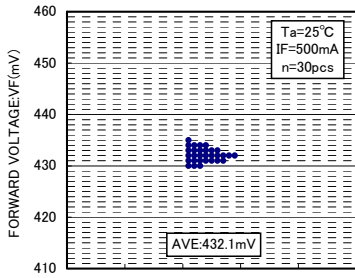
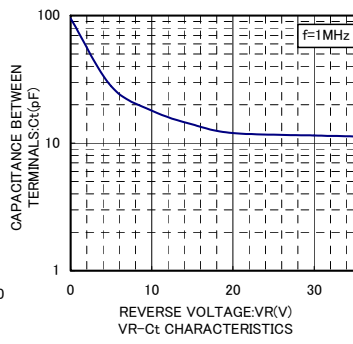
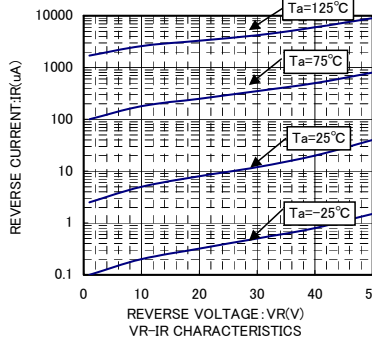
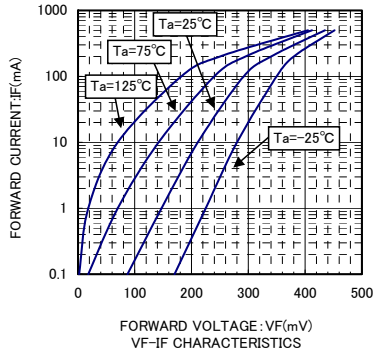
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	$V_{RM}$	50	V
Reverse voltage (DC)	$V_R$	20	V
Average rectified forward current	$I_o$	0.5	A
Forward current surge peak (60Hz·1cyc)	$I_{FSM}$	3	A
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40 to +125	°C

●Electrical characteristics (Ta=25°C)

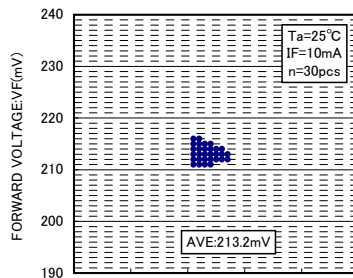
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{F1}$	-	-	0.50	V	$I_F=500mA$
	$V_{F2}$	-	-	0.30	V	$I_F=10mA$
Reverse current	$I_R$	-	-	30	μA	$V_R=10V$
Capacitance between terminals	$C_t$	-	20	-	pF	$V_R=10V, f=1MHz$

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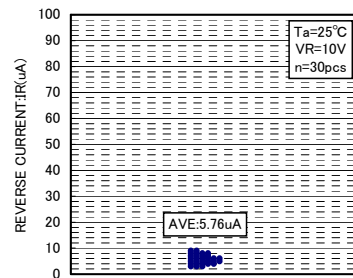
●Electrical characteristic curves (Ta=25°C)



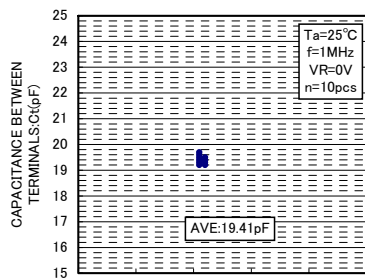
VF DISPERSION MAP



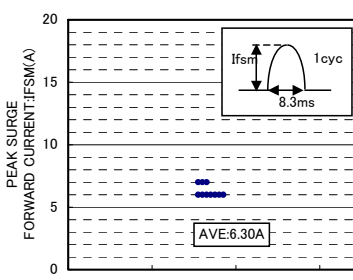
VF DISPERSION MAP



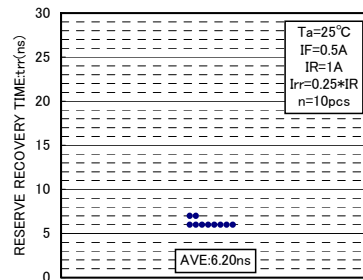
IR DISPERSION MAP



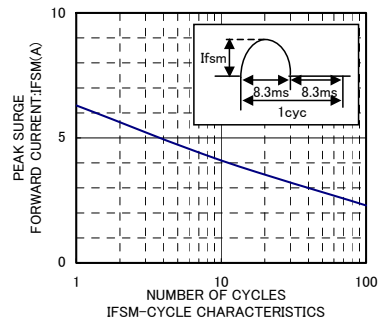
Ct DISPERSION MAP



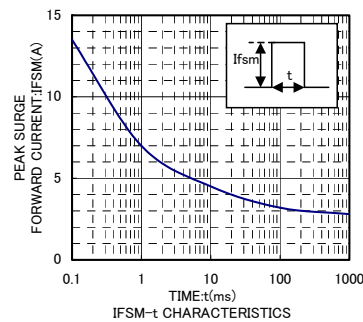
IFSM DISERSION MAP



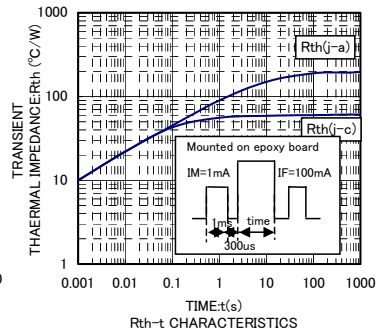
trr DISPERSION MAP



IFSM-CYCLE CHARACTERISTICS

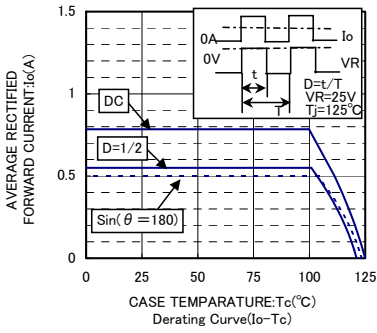
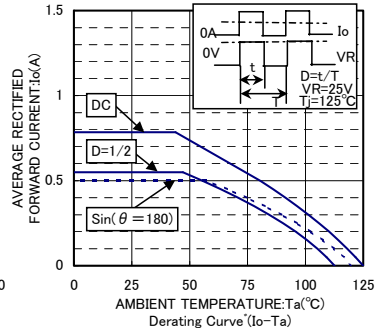
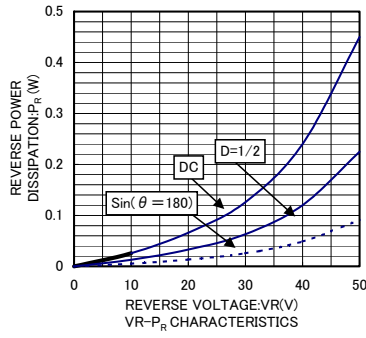
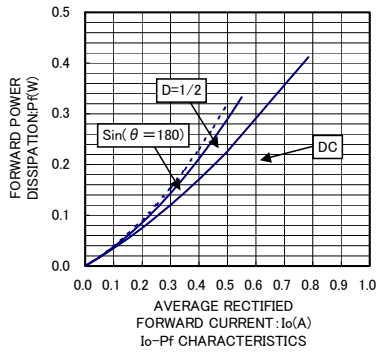


IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS

Diodes



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